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Carrier relaxation with LO phonon decay in semiconductor quantum dots

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Abstract Analysis of an exactly soluble model of phonons coupled to a carrier in a quantum dot provides a clear illustration of a phonon bottleneck to relaxation. The introduction of three-phonon interactions leads to a broad window for relaxation by the processes of LO phonon scattering and decay.

1 Introduction

The possible existence of a phonon "bottleneck" that might inhibit the relaxation of carriers in quantum dots remains a subject of controversy. Although the bottleneck is readily eliminated from theoretical treatments by the introduction of non-phonon scattering processes, there has also been interest in demonstrating relaxation by intrinsic phonon scattering mechanisms alone.

Within the one-phonon approximation to the self-energy, the carrier's spectral function (density of states) consists of a number of peaks which broaden rapidly with increasing temperature. This level broadening is known not to be a lifetime effect [1], but might be supposed to help relieve the constraint of exact level matching in LO phonon emission. Indeed, the non-vanishing relaxation rates found in simple non-equilibrium treatments [2,3] can be traced to the non-vanishing spectral widths of the one-particle Green's function.

Though physically plausible, such theories conflict with the results of experiments by predicting a vanishingly small relaxation rate in the limit of low temperature and low excitation density, where Auger processes can be neglected. For this reason we have made a one-phonon calculation of the carrier's spectral function in an exactly soluble model for which we know that there can be *no* relaxation, as will be explained in Sect. 2 below. Figure 1 illustrates the broadening of the spectral peaks that—in this case, at least—is a spurious result due to the one-phonon approximation. Accordingly, one should regard with caution any proposed relaxation mechanism that relies on the broadening obtained in this widely-used approximation.

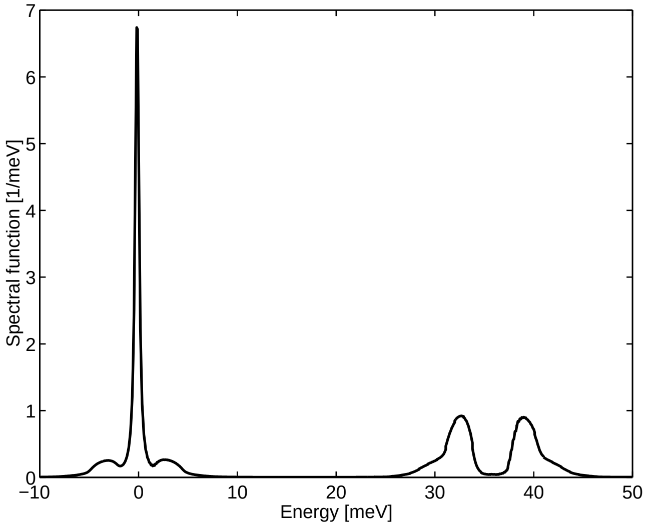

Fig. 1 Electronic spectral function at 300 K for an unperturbed level separation $\Delta = \hbar\omega_0 = 36\,\text{meV}$. The electron–phonon interaction is responsible for the Rabi splitting of the peak for the first excited state.

Despite the impossibility (in our model) of obtaining relaxation by LO-phonon emission alone, we show in Sect. 3 that the introduction of three-phonon interactions (leading, e.g., to the decay of an LO phonon to give two LA phonons) can give a broad, temperature-dependent window for relaxation, as was found previously [4] by use of the Wigner–Weisskopf method.

2 A soluble model

Our model for phonons interacting with an electron in a parabolic confining potential is the usual electron–phonon Hamiltonian with a special choice of matrix elements $\sqrt{n+1}\,g_q$ between neighbouring electron levels,

$$H = \Delta \sum_n n\, c_n^\dagger c_n + \sum_q \hbar\omega_q b_q^\dagger b_q + \sum_{n,q} \sqrt{n+1}\, g_q \big(b_q + b_{-q}^\dagger\big)\big(c_{n+1}^\dagger c_n + c_n^\dagger c_{n+1}\big)\,, \qquad (1)$$

where c_n and b_q are the electron and phonon annihilation operators. The calculation of the spectral function illustrated in Fig. 1 was based on Eq. (1), truncated to four levels. In the one-electron subspace, the ladder operators $a = \sum_n \sqrt{n+1}\, c_n^\dagger c_{n+1}$ and $a^\dagger$ obey Bose commutation rules and the above Hamiltonian is equivalent to

$$H = \Delta a^\dagger a + \sum_q \big\{\hbar\omega_q b_q^\dagger b_q + g_q\big(b_q + b_{-q}^\dagger\big)\big(a + a^\dagger\big)\big\}\,. \qquad (2)$$

The Hamiltonian (2) represents a system of coupled oscillators, so that all features of its energy spectrum and response can be obtained without approximation. For example, the response to an impulsive electric field applied at time $t = 0$ is given by the retarded susceptibility

$$\chi(t) = -i\langle X(t)X(0) - X(0)X(t)\rangle\,\theta(t)\,, \qquad (3)$$

where $X = a + a^\dagger$ is proportional to the electron dipole moment and $\theta(t)$ is the unit step function. In the frequency domain, χ satisfies the Dyson equation

$$\chi(\omega) = \chi^0(\omega) + \chi^0(\omega) \textstyle\sum_q |g_q|^2 D_q^0(\omega)\, \chi(\omega)\,, \tag{4}$$

which can be solved for $\chi(\omega)$ in terms of the unperturbed phonon Green's functions $D_q^0(\omega)$.

For coupling to dispersionless LO phonons the calculation can be completed analytically. The spectral function $-2\,\mathrm{Im}\,\chi(\omega)$ consists of a pair of (Rabi split) delta-function peaks that result from the binding of a phonon to the electron [1]. In the time domain, $\chi(t)$ is the sum of two undamped oscillations: the electric field excites the electron into a state which is a superposition of exact eigenstates from the discrete spectrum of (2), and from which the electron is unable to relax.

For coupling to LA phonons, the sum appearing in (4) can be evaluated numerically. We find that if Δ falls in the LA phonon continuum, relaxation is possible by emission of an LA phonon, but the rate is many orders of magnitude too slow for single LA-phonon emission to be significant as a mechanism for relaxation.

3 Influence of three-phonon interactions

Finally we turn to mechanisms that can lead to the fast relaxation of an electron in a quantum dot. Interactions between phonons of branches i, j, and k can be described by a phenomenological Hamiltonian [5]

$$H^{ijk} = \beta \sum_{p+q+r=0} \omega_p^i\, \omega_q^j\, \omega_r^k\, X_p^i\, X_q^j\, X_r^k\,, \tag{5}$$

where $X_p^i = \left(b_p^i + b_{-p}^{i\,\dagger}\right)/\left(M^i\omega_p^i\right)^{1/2}$. We choose the coefficient β (the same for all ijk) to obtain agreement with the observed lifetime of free LO phonons with respect to decay to two LA phonons, $\tau = 2.5\,\mathrm{ps}$ in GaAs at 300 K. Note that we must, more generally, consider also the interactions with $i = \mathrm{LA}$ and $j = k = \mathrm{LO}$, because an LO phonon bound to an electron can be liberated by absorption or emission of an LA phonon with simultaneous relaxation of the electron. In contrast, non-dispersive free LO phonons cannot be scattered in this way because of the constraint of energy conservation.

The effect of the interactions is calculated perturbatively. The LO-phonon Green's function $D_q(\omega)$ satisfies a Dyson equation

$$D_q(\omega) = D_q^0(\omega) + D_q^0(\omega)\, \Pi_q(\omega)\, D_q(\omega)\,, \tag{6}$$

where the phonon self-energy $\Pi_q(\omega)$ is evaluated to second order in β by use of the Matsubara technique [6]. The phonon Green's function obtained in this way replaces $D_q^0(\omega)$ in Eq. (4), which gives an approximation for the susceptibility for the electron. A relaxation rate for the electron is estimated by fitting an exponential [4] to the time-domain susceptibility, $\chi(t)$.

Results of these calculations are shown in Fig. 2, for temperatures $T = 0$ and 300 K, and for a range of electron level separations. In all cases the relaxation rate is greatest when the unperturbed level separation matches the LO phonon energy, $\Delta \simeq \hbar\omega_0$. This is understandable on qualitative grounds, as in this region the electron–phonon bound-state wave function contains nearly equal amplitudes for the electron to be in its ground state (with one additional phonon) as in its first excited state, so that the interaction Hamiltonian has a large matrix element between the bound state and the electron ground state. A new result of our work is that the relaxation rate remains high only up to a threshold value of Δ beyond which the energy conservation law cannot be satisfied; in fact, as can be seen from the graph, there are slightly different thresholds for the two kinds of relaxation process considered.

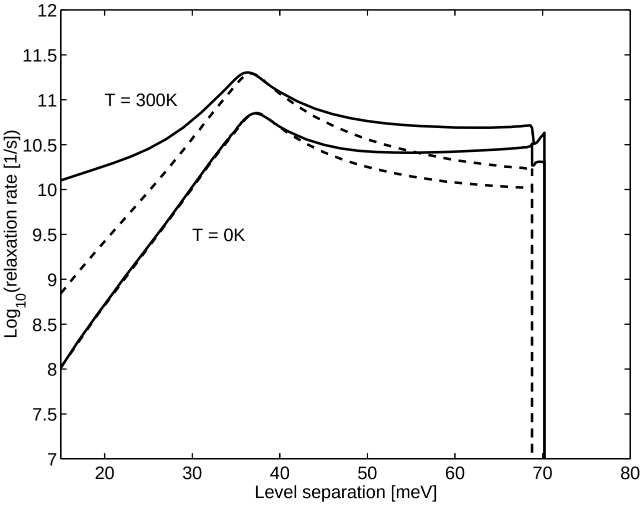

Fig. 2 Carrier relaxation rate as a function of level separation. Dashed lines are results for the mechanism LO → 2 LA ; results shown by solid lines also include LO → LO ± LA.

The scattering process LO → LO − LA has a particularly strong dependence on temperature. Below resonance, it leads to no enhancement to the relaxation rate at low temperature because there are few LA phonons available to be absorbed. In contrast, at 300 K the absorption of LA phonons enhances the relaxation rate by more than an order of magnitude at the smallest values of Δ, and so provides the major route for relaxation in this régime.

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